

# BC847BM3T5G

Preferred Device

## General Purpose Transistor

### NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-723 package which is designed for low power surface mount applications.

- This is a Pb-Free Device

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	45	V
Collector-Base Voltage	$V_{CBO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current - Continuous	$I_C$	100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) $T_A = 25^\circ\text{C}$ Derated above $25^\circ\text{C}$	$P_D$	260 2.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	480	$^\circ\text{C}/\text{W}$
Total Device Dissipation, FR-4 Board (Note 2) $T_A = 25^\circ\text{C}$ Derated above $25^\circ\text{C}$	$P_D$	600 4.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	205	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

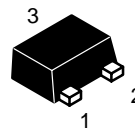
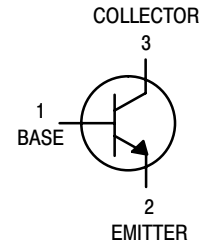
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad
2. FR-4 @  $1.0 \times 1.0$  Inch Pad



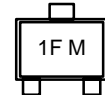
ON Semiconductor®

<http://onsemi.com>



SOT-723  
CASE 631AA  
STYLE 1

#### MARKING DIAGRAM



1F = Device Code  
M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
BC847BM3T5G	SOT-723	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BC847BM3T5G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ )	$V_{(BR)CEO}$	45	–	–	V
Collector–Emitter Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ , $V_{EB} = 0$ )	$V_{(BR)CES}$	50	–	–	V
Collector–Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ )	$V_{(BR)CBO}$	50	–	–	V
Emitter–Base Breakdown Voltage ( $I_E = 1.0\ \mu\text{A}$ )	$V_{(BR)EBO}$	6.0	–	–	V
Collector Cutoff Current ( $V_{CB} = 30\text{ V}$ ) ( $V_{CB} = 30\text{ V}$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	–	–	15 5.0	nA $\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 10\ \mu\text{A}$ , $V_{CE} = 5.0\text{ V}$ ) ( $I_C = 2.0\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ )	$h_{FE}$	– 200	150 290	– 450	–
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ ) ( $I_C = 100\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{CE(sat)}$	– –	– –	0.25 0.6	V
Base–Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ ) ( $I_C = 100\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{BE(sat)}$	– –	0.7 0.9	– –	V
Base–Emitter Voltage ( $I_C = 2.0\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ )	$V_{BE(on)}$	580 –	660 –	700 770	mV
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Current–Gain – Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	–	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	–	4.5	pF
Noise Figure ( $I_C = 0.2\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $BW = 200\text{ Hz}$ )	NF	–	–	10	dB

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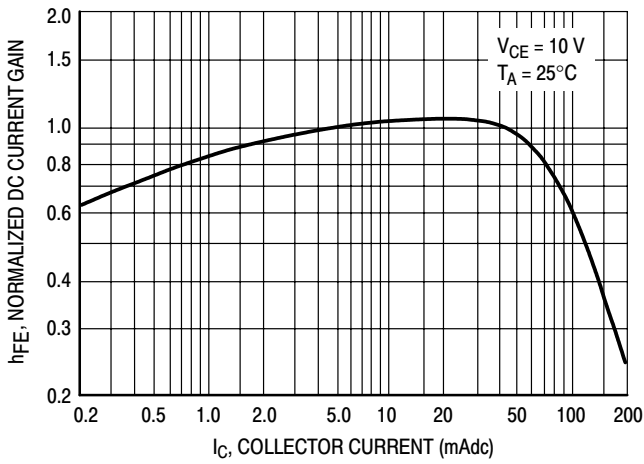


Figure 1. Normalized DC Current Gain

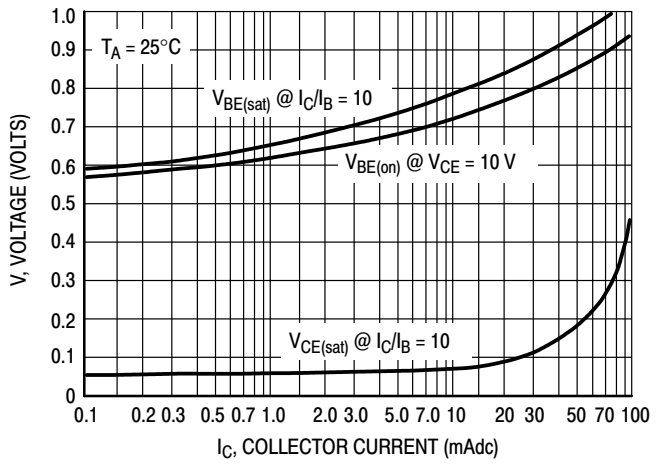


Figure 2. "Saturation" and "On" Voltages

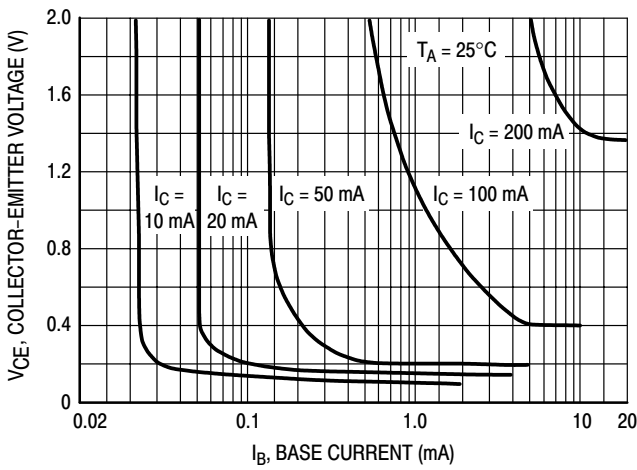


Figure 3. Collector Saturation Region

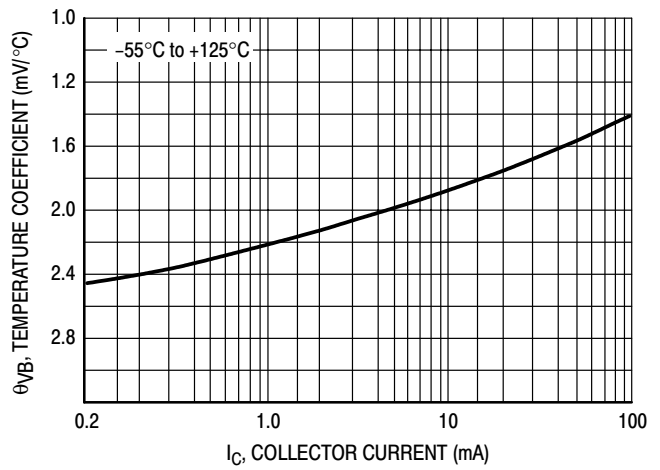


Figure 4. Base-Emitter Temperature Coefficient

# BC847BM3T5G

## BC847

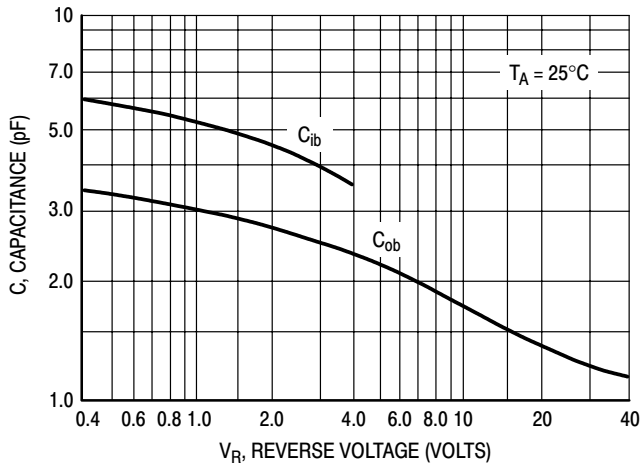


Figure 5. Capacitances

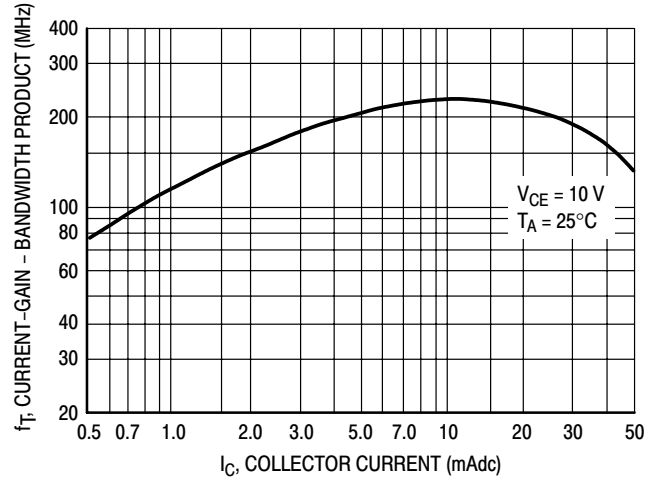
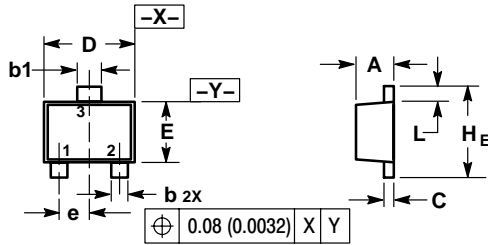


Figure 6. Current-Gain - Bandwidth Product

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## PACKAGE DIMENSIONS

SOT-723  
CASE 631AA-01  
ISSUE B



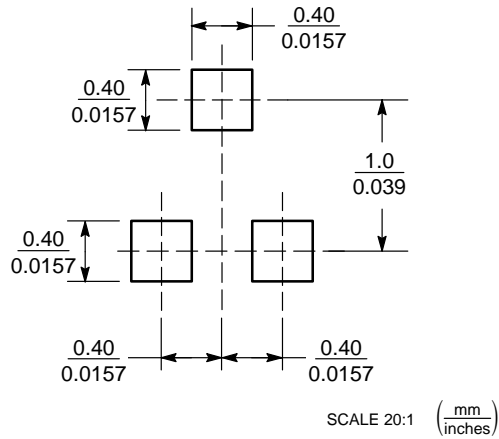
### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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